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Manufacturers of World Class Discrete Semiconductors

2N4406

2N4407

PNP SILICON TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4406, 2N4407 types are PNP Silicon Epitaxial Planar Transistors designed for general purpose and switching applications.

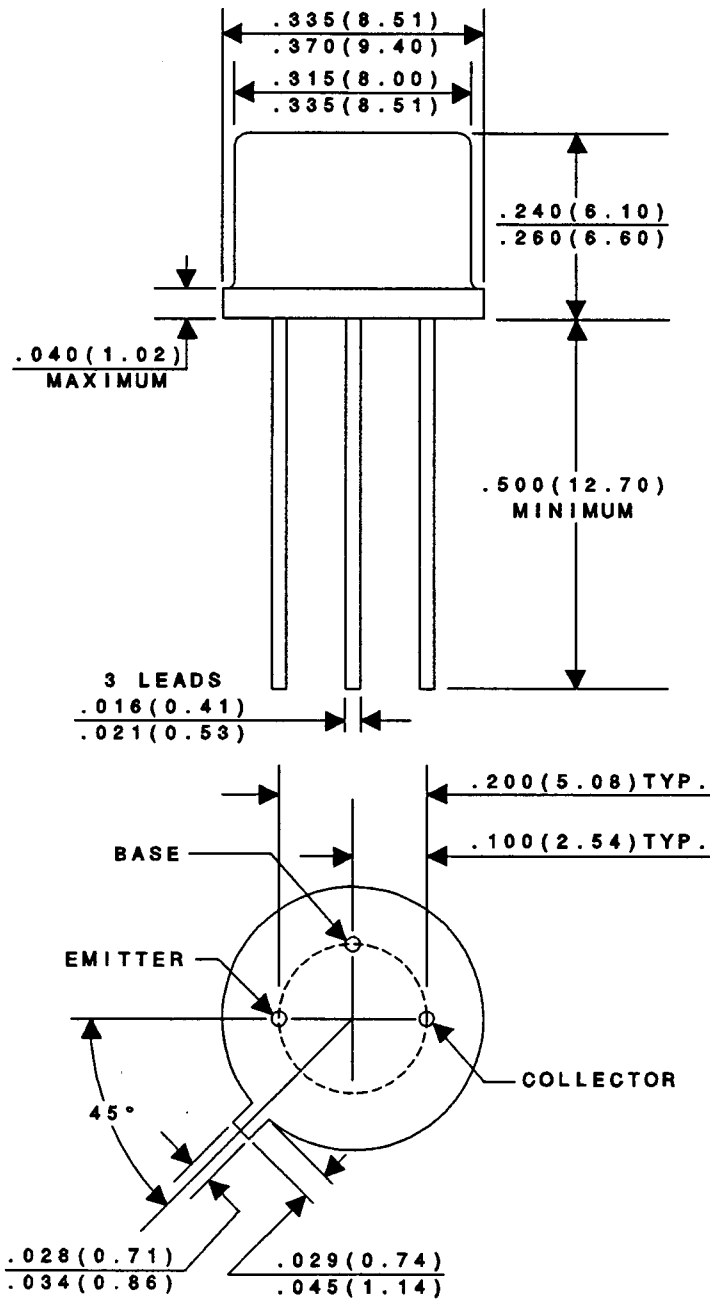
MAXIMUM RATINGS (T_A = 25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	80	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	2.0	A
Power Dissipation	P _D	1.25	W
Power Dissipation (T _C = 25°C)	P _D	8.75	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +200	°C
Thermal Resistance	θ _{JA}	140	°C/W
Thermal Resistance	θ _{JC}	20	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N4406		2N4407		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} = 60V		25		25	μA
I _{EBO}	V _{EB} = 3.0V		25		25	μA
BV _{CEO}	I _C = 10mA	80		80		V
BV _{CBO}	I _C = 10μA	80		80		V
BV _{EBO}	I _E = 10μA	5.0		5.0		V
V _{CE(SAT)}	I _C = 150mA, I _B = 15mA		0.2		0.2	V
V _{CE(SAT)}	I _C = 500mA, I _B = 50mA		0.4		0.4	V
V _{CE(SAT)}	I _C = 1.0A, I _B = 100mA		0.7		0.7	V
V _{CE(SAT)}	I _C = 1.5A, I _B = 150mA		1.5		1.5	V
V _{BE(SAT)}	I _C = 150mA, I _B = 15mA		0.9		0.9	V
V _{BE(SAT)}	I _C = 1.0A, I _B = 100mA		1.3		1.3	V
V _{BE(SAT)}	I _C = 1.5A, I _B = 150mA		1.5		1.5	V
V _{BE(ON)}	V _{CE} = 1.0V, I _C = 500mA		1.0		1.0	V
h _{FE}	V _{CE} = 5.0V, I _C = 10mA	30		80		
h _{FE}	V _{CE} = 5.0V, I _C = 150mA	30		80		
h _{FE}	V _{CE} = 5.0V, I _C = 500mA	30	120	80	240	
h _{FE}	V _{CE} = 5.0V, I _C = 1.0A	20		30		
h _{FE}	V _{CE} = 5.0V, I _C = 1.5A	10		10		
f _T	V _{CE} = 20V, I _C = 50mA, f = 100MHz	50		50		MHz
C _{cb}	V _{CB} = 10V, I _E = 0, f = 1.0MHz		50		50	pF

JEDEC TO-39 CASE - MECHANICAL DIMENSIONS



All Dimensions in Inches (mm).